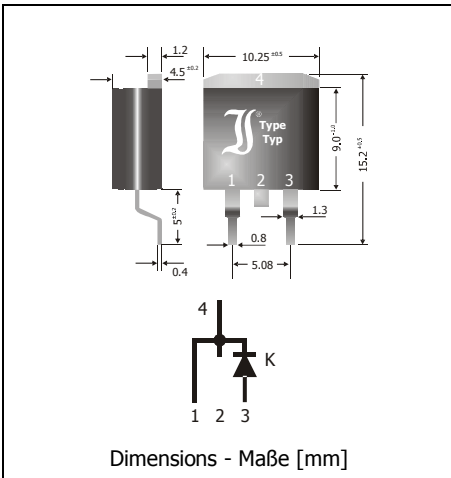


**UGB8AT ... UGB8JT**  
**Superfast Efficient Rectifiers – Single Diode**  
**Superschnelle Hocheffizienz-Gleichrichter – Einzeldiode**

Version 2012-10-09



Nominal current Nennstrom	8 A
Repetitive peak reverse voltage Periodische Spitzensperrspannung	50...600 V
Plastic case Kunststoffgehäuse	TO-263AB D <sup>2</sup> PAK (D2)
Weight approx. Gewicht ca.	1.6 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	
Standard packaging in tubes Standard Lieferform in Stangen	

**Maximum ratings and Characteristics**

**Grenz- und Kennwerte**

Type Typ	Repetitive peak reverse voltage Periodische Spitzensperrspannung $V_{RRM}$ [V]	Surge peak reverse voltage Stoßspitzensperrspannung $V_{RSM}$ [V]	Forward voltage Durchlass-Spannung $V_F$ [V] <sup>1)</sup>	
			$I_F = 5 A$	$I_F = 8 A$
UGB8AT	50	50	< 0.9	< 1.0
UGB8BT	100	100	< 0.9	< 1.0
UGB8DT	200	200	< 0.9	< 1.0
UGB8GT	400	400	< 1.15	< 1.25
UGB8JT	600	600	< 1.6	< 1.75

Max. average forward rectified current, R-load Dauergrenzstrom in Einwegschaltung mit R-Last	$T_C = 100^\circ C$	$I_{FAV}$	8 A
Repetitive peak forward current Periodischer Spitzenstrom	$f > 15 Hz$	$I_{FRM}$	22 A <sup>2)</sup>
Peak forward surge current, 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwellen	$T_A = 25^\circ C$	$I_{FSM}$	112/125 A
Rating for fusing, $t < 10 ms$ Grenzlastintegral, $t < 10 ms$	$T_A = 25^\circ C$	$i^2t$	62 A <sup>2</sup> s
Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		$T_j$ $T_s$	-50...+150°C -50...+175°C

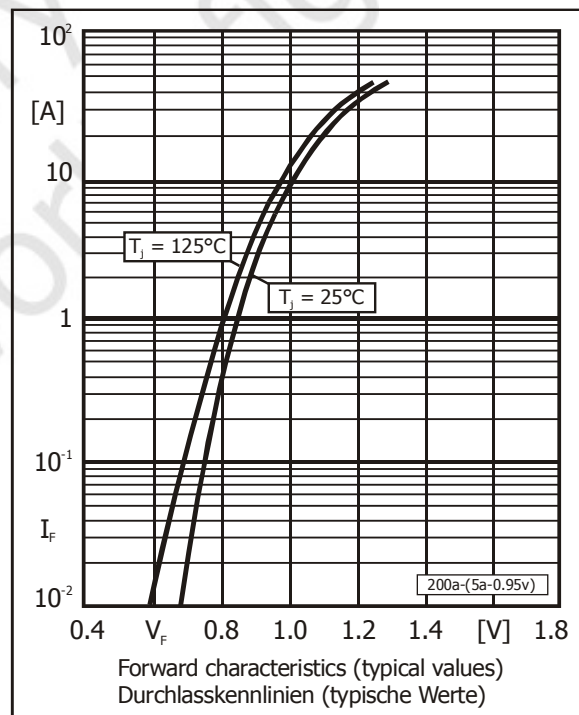
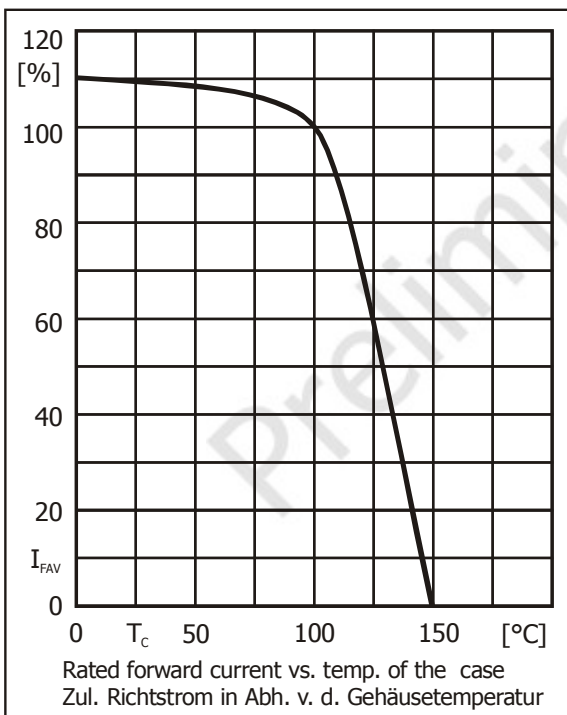
1  $T_j = 25^\circ C$

2 Max. temperature of the case  $T_C = 100^\circ C$  – Max. Temperatur des Gehäuses  $T_C = 100^\circ C$

**Characteristics**
**Kennwerte**

Type Typ	Reverse recovery time Sperrverzugszeit	Reverse recovery time Sperrverzugszeit
	$T_j = 25^\circ\text{C}$	$T_j = 25^\circ\text{C}$
	$t_{rr} [\text{ns}]^1)$	$t_{rr} [\text{ns}]^2)$
UGB8AT ... UGB8DT	< 25	< 35
UGB8GT ... UGB8JT	< 35	< 45

Leakage current Sperrstrom	$T_j = 25^\circ\text{C}$ $V_R = V_{RRM}$	$I_R$	< 5 $\mu\text{A}$
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse		$R_{thc}$	< 2.5 K/W



1  $I_F = 0.5 \text{ A}$  through/über  $I_R = 1 \text{ A}$  to/auf  $I_R = 0.25 \text{ A}$   
 2  $I_F = 1.0 \text{ A}$ ,  $di/dt = -50 \text{ A}/\mu\text{s}$ ,  $V_R = 30 \text{ V}$